

6.5 A metal contains N voids/cm³ of radius R and a dislocation density ρ . The metal is subject to a hydrostatic *tensile* stress σ which causes the dislocations and voids to exchange vacancies.

What is the swelling rate? Assume that the self-diffusion coefficient of the metal, D , is known.

- vacancy conservation equation in terms of the fluxes of vacancies to or from the voids and dislocations

$$J_V^d \rho = J_V^C N \quad (1)$$

- driving forces for vacancy flows to and from the defects

$$\text{Voids: } \pm \left[C_V - C_V^{\text{eq}} \exp\left(\frac{2\gamma}{R} \frac{\Omega}{kT}\right) \right] \quad \text{disl.} \quad \pm \left[C_V^{\text{eq}} \exp\left(\frac{\sigma\Omega}{kT}\right) - C_V \right]$$

vacancy fluxes:

$$J_V^C = 4\pi R D_V \left[C_V - C_V^{\text{eq}} \exp\left(\frac{2\gamma}{R} \frac{\Omega}{kT}\right) \right] \approx 4\pi R D_V \left[C_V - C_V^{\text{eq}} \left(1 + \frac{2\gamma}{R} \frac{\Omega}{kT}\right) \right] \quad (2a)$$

(per void)

$$J_V^d = Z_V D_V \left[C_V^{\text{eq}} \exp\left(\frac{\sigma\Omega}{kT}\right) - C_V \right] \approx Z_V D_V \left[C_V^{\text{eq}} \left(1 + \frac{\sigma\Omega}{kT}\right) - C_V \right] \quad (2b)$$

(per unit length)

Substitute (2a) & (2b) into (1) & solve for C_V ; insert in (2a)

Swelling rate: $d(\Delta V/V)/dt = J_V^C N \Omega$

Insert sol'n for C_V into (2a):

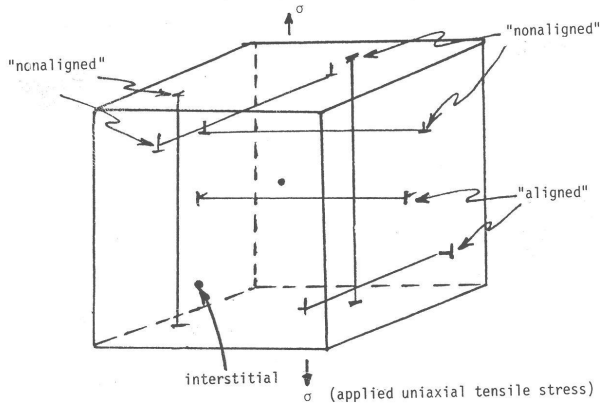
$$\frac{d}{dt} \left(\frac{\Delta V}{V} \right) = D \left[\frac{(Z_V \rho)(4\pi R N)}{Z_V \rho + 4\pi R N} \right] \frac{\Omega}{kT} \left(\sigma - \frac{2\gamma}{R} \right)$$

$$D = D_V C_V^{\text{eq}} \Omega$$

- swelling largest if $Z_V \rho \gg 4\pi R N$

- if $\sigma > 2\gamma/R$, swelling; if $\sigma < 2\gamma/R$, shrinkage

7.4 SIPA creep with voids/recombination



$$Z_{I(a)} - Z_{I(na)} = \alpha(c_a - c_{na})\sigma$$

$$\dot{\epsilon}_{\text{SIPA}} = \frac{2}{9}\rho\Omega D_I C_I (Z_{I(a)} - Z_{I(na)}) = \frac{2}{9}\rho\Omega D_I C_I \alpha (c_a - c_{na})\sigma$$

Point defect balances:

$$\text{All } Z_i = 1$$

1. With voids: $K/\Omega = \rho D_I C_I + 4\pi R N D_I C_I$

Solve for $D_I C_I$:

$$D_I C_I = \frac{K/\Omega}{\rho + 4\pi R N}$$

Next step:

$$\dot{\epsilon}_{\text{SIPA}} = \frac{\frac{2}{9}\alpha\Delta c K}{1 + 4\pi R N/\rho} \sigma$$

If $4\pi R N \ll \rho$, original SIPA formula recovered

2. With recombination: $K/\Omega = \rho D_I C_I + k_R C_V C_I$

Vacancy balance: $K/\Omega = \rho D_V C_V + k_R C_V C_I$

Solution $D_I C_I = D_V C_V$

Use above eqn to eliminate C_V from I balance; solve for C_I

$$D_I C_I = \frac{\left[(\rho D_I D_V)^2 + 4k_R D_I D_V (K/\Omega) \right]^{1/2} - \rho D_I D_V}{2k_R}$$

Substitute into $\dot{\epsilon}_{SIPA}$ formula:

$$\frac{\dot{\epsilon}_{SIPA} \text{ (with recomb.)}}{\dot{\epsilon}_{SIPA} \text{ (without recomb.)}} = \frac{\sqrt{1 + 2E} - 1}{E}$$

$$E = \frac{2k_R (K/\Omega)}{\rho^2 D_I D_V}$$

T ↓

$E \gg 1$

no SIPA creep

T ↑

$E \ll 1$

no effect of recomb.